

WHAT IS CLAIMED IS:

1. A method of fabricating a semiconductor integrated circuit device that has a standby current of 5 μ A or below in tests of operation at 90°C and has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:
 - (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode by patterning the silicon film deposited on said gate insulating film;
 - (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
 - (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions;
 - (e) forming a metal film on said source/drain regions;
 - (f) forming a metallic silicide layer where said source/drain regions are in contact with said metal film; and
 - (g) removing that part of said metal film which did not react in step (f).
2. A method of fabricating a semiconductor integrated circuit device, as defined in claim 1, wherein a sidewall film is formed on the surfaces of the sides of

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said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.

3. A method of fabricating a semiconductor integrated circuit device, as defined in claim 1, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.
4. A method of fabricating a semiconductor integrated circuit device, as defined in claim 1, wherein said sputter etching is Ar sputter etching.
5. A method of fabricating a semiconductor integrated circuit device, as defined in claim 1, wherein said metal film is a film of Co.
6. A method of fabricating a semiconductor integrated circuit device, as defined in claim 1, wherein said MISFETs configure an SRAM memory cell.
7. A method of fabricating a semiconductor integrated circuit device, as defined in claim 1, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.

8. A method of fabricating a semiconductor integrated circuit device that has a standby current of 5 μ A or below in tests of operation at 90°C and has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:
 - (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode by patterning the silicon film deposited on said gate insulating film;
 - (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
 - (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions;
 - (e) forming a metal film on said source/drain regions and on said gate electrode;
 - (f) forming a metallic silicide layer where said source/drain regions are in contact with said metal film and where said gate electrode are in contact with said metal film, and
 - (g) removing that part of said metal film which did not react in step (f).
9. A method of fabricating a semiconductor integrated circuit device, as defined in claim 8, wherein a sidewall film is formed on the surfaces of the sides of

said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.

10. A method of fabricating a semiconductor integrated circuit device, as defined in claim 8, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.
11. A method of fabricating a semiconductor integrated circuit device, as defined in claim 8, wherein said sputter etching is Ar sputter etching.
12. A method of fabricating a semiconductor integrated circuit device, as defined in claim 8, wherein said metal film is a film of Co.
13. A method of fabricating a semiconductor integrated circuit device, as defined in claim 8, wherein said MISFETs configure an SRAM memory cell.
14. A method of fabricating a semiconductor integrated circuit device, as defined in claim 8, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.

09974814-10101
T02T0T-4T842660

15. A method of fabricating a semiconductor integrated circuit device and has MISFETs formed on the main surface of a semiconductor substrate which has a standby current of 1.5 μ A or below in actual operation, comprising the steps of:
- (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode by patterning the silicon film deposited on said gate insulating film;
 - (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
 - (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions;
 - (e) forming a metal film on said source/drain regions;
 - (f) forming a metallic silicide layer where said source/drain regions are in contact with said metal film; and
 - (g) removing that part of said metal film which did not react in step (f).
16. A method of fabricating a semiconductor integrated circuit device, as defined in claim 15, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.

09974814-101201
T02T0T-4T842660

17. A method of fabricating a semiconductor integrated circuit device, as defined in claim 15, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.
18. A method of fabricating a semiconductor integrated circuit device, as defined in claim 15, wherein said sputter etching is Ar sputter etching.
19. A method of fabricating a semiconductor integrated circuit device, as defined in claim 15, wherein said metal film is a film of Co.
20. A method of fabricating a semiconductor integrated circuit device, as defined in claim 15, wherein said MISFETs configure an SRAM memory cell.
21. A method of fabricating a semiconductor integrated circuit device, as defined in claim 15, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.
22. A method of fabricating a semiconductor integrated circuit device that has a standby current of 1.5 μ A or

below in actual operation and has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:

- (a) forming a gate-insulating film on said semiconductor substrate;
- (b) forming a gate electrode by patterning the silicon film deposited on said gate insulating film;
- (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
- (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions;
- (e) forming a metal film on said source/drain regions and on said gate electrode;
- (f) forming a metallic silicide layer where said source/drain regions are in contact with said metal film and where said gate electrode are in contact with said metal film, and
- (g) removing that part of said metal film which did not react in step (f).

23. A method of fabricating a semiconductor integrated circuit device, as defined in claim 22, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.

24. A method of fabricating a semiconductor integrated circuit device, as defined in claim 22, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.

25. A method of fabricating a semiconductor integrated circuit device, as defined in claim 22, wherein said sputter etching is Ar sputter etching.

26. A method of fabricating a semiconductor integrated circuit device, as defined in claim 22, wherein said metal film is a film of Co.

27. A method of fabricating a semiconductor integrated circuit device, as defined in claim 22, wherein said MISFETs configure an SRAM memory cell.

28. A method of fabricating a semiconductor integrated circuit device, as defined in claim 22, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.

29. A method of fabricating a semiconductor integrated circuit device that is battery-driven and has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:

- (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode by patterning the silicon film deposited on said gate insulating film;
 - (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
 - (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions;
 - (e) forming a metal film on said source/drain regions;
 - (f) forming a metallic silicide layer where said source/drain regions are in contact with said metal film; and
 - (g) removing that part of said metal film which did not react in step (f).
30. A method of fabricating a semiconductor integrated circuit device, as defined in claim 29, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.
31. A method of fabricating a semiconductor integrated circuit device, as defined in claim 29, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.

32. A method of fabricating a semiconductor integrated circuit device, as defined in claim 29, wherein said sputter etching is Ar sputter etching.
33. A method of fabricating a semiconductor integrated circuit device, as defined in claim 29, wherein said metal film is a film of Co.
34. A method of fabricating a semiconductor integrated circuit device, as defined in claim 29, wherein said MISFETs configure an SRAM memory cell.
35. A method of fabricating a semiconductor integrated circuit device, as defined in claim 29, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.
36. A method of fabricating a semiconductor integrated circuit device that is battery-driven and has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:
 - (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode by patterning the silicon film deposited on said gate insulating film;

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- (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
 - (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions;
 - (e) forming a metal film on said source/drain regions and on said gate electrode;
 - (f) forming a metallic silicide layer where said source/drain regions are in contact with said metal film and where said gate electrode are in contact with said metal film, and
 - (g) removing that part of said metal film which did not react in step (f).

37. A method of fabricating a semiconductor integrated circuit device, as defined in claim 36, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.

38. A method of fabricating a semiconductor integrated circuit device, as defined in claim 36, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.

39. A method of fabricating a semiconductor integrated circuit device, as defined in claim 36, wherein said sputter etching is Ar sputter etching.
40. A method of fabricating a semiconductor integrated circuit device, as defined in claim 36, wherein said metal film is a film of Co.
41. A method of fabricating a semiconductor integrated circuit device, as defined in claim 36, wherein said MISFETs configure an SRAM memory cell.
42. A method of fabricating a semiconductor integrated circuit device, as defined in claim 36, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.
43. A method of fabricating a semiconductor integrated circuit device that has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:
- (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode with a width of 0.18 μm or less by patterning the silicon film that has been deposited on said gate-insulating film;

09974814-101201
FOOTNOTE "47842660

- (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
- (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions;
- (e) forming a metal film on said source/drain regions;
- (f) forming a metallic silicide layer with a thickness of 20 to 40 nm where said source/drain regions are in contact with said metallic film; and
- (g) removing that part of said metal film which did not react in step (f).

- 44. A method of fabricating a semiconductor integrated circuit device, as defined in claim 43, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.
- 45. A method of fabricating a semiconductor integrated circuit device, as defined in claim 43, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.
- 46. A method of fabricating a semiconductor integrated circuit device, as defined in claim 43, wherein said sputter etching is Ar sputter etching.

47. A method of fabricating a semiconductor integrated circuit device, as defined in claim 43, wherein said metal film is a film of Co.
48. A method of fabricating a semiconductor integrated circuit device, as defined in claim 43, wherein said MISFETs configure an SRAM memory cell.
49. A method of fabricating a semiconductor integrated circuit device, as defined in claim 43, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.
50. A method of fabricating a semiconductor integrated circuit device that is battery-driven and has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:
 - (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode with a width of 0.18 μm or less by patterning the silicon film that has been deposited on said gate-insulating film;
 - (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;

(d) sputter-etching away the top of said source/drain regions and on said gate electrode to 2.5 nm or less below the surface of the regions;

(e) forming a metal film on said source/drain regions and on said gate electrode;

(f) forming a metallic silicide layer with a thickness of 20 to 40 nm where said source/drain regions are in contact with said metallic film and where said gate electrode are in contact with said metal film; and

(g) removing that part of said metal film which did not react in step (f).

51. A method of fabricating a semiconductor integrated circuit device, as defined in claim 50, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.
52. A method of fabricating a semiconductor integrated circuit device, as defined in claim 50, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.
53. A method of fabricating a semiconductor integrated circuit device, as defined in claim 50, wherein said sputter etching is Ar sputter etching.

09974814-101201

54. A method of fabricating a semiconductor integrated circuit device, as defined in claim 50, wherein said metal film is a film of Co.
55. A method of fabricating a semiconductor integrated circuit device, as defined in claim 50, wherein said MISFETs configure an SRAM memory cell.
56. A method of fabricating a semiconductor integrated circuit device, as defined in claim 50, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.
57. A method of fabricating a semiconductor integrated circuit device that has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:
- (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode with a width of 0.18 μm or less by patterning the silicon film that has been deposited on said gate-insulating film;
 - (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
 - (d) sputter-etching away the top of said source/drain

regions to 2.5 nm or less below the surface of the regions;

(e) forming a metal film on said source/drain regions;

(f) forming a metallic silicide layer with sheet resistance of $5\Omega/\square$ to $12\Omega/\square$, where said source/drain regions are in contact with said metal film; and

(g) removing that part of said metal film which did not react in step (f).

58. A method of fabricating a semiconductor integrated circuit device, as defined in claim 57, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.

59. A method of fabricating a semiconductor integrated circuit device, as defined in claim 57, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.

60. A method of fabricating a semiconductor integrated circuit device, as defined in claim 57, wherein said sputter etching is Ar sputter etching.

0994814 101201
FOOTNOTES

61. A method of fabricating a semiconductor integrated circuit device, as defined in claim 57, wherein said metal film is a film of Co.
62. A method of fabricating a semiconductor integrated circuit device, as defined in claim 57, wherein said MISFETs configure an SRAM memory cell.
63. A method of fabricating a semiconductor integrated circuit device, as defined in claim 57, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.
64. A method of fabricating a semiconductor integrated circuit device that is battery-driven and has MISFETs formed on the main surface of a semiconductor substrate, comprising the steps of:
 - (a) forming a gate-insulating film on said semiconductor substrate;
 - (b) forming a gate electrode with a width of 0.18 μm or less by patterning the silicon film that has been deposited on said gate-insulating film;
 - (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate;
 - (d) sputter-etching away the top of said source/drain

regions and on said gate electrode to 2.5 nm or less below the surface of the regions;

(e) forming a metal film on said source/drain regions and on said gate electrode;

(f) forming a metallic silicide layer with sheet resistance of $5\Omega/\square$ to $12\Omega/\square$, where said source/drain regions are in contact with said metal film and where said gate electrode are in contact with said metal film; and

(g) removing that part of said metal film which did not react in step (f).

65. A method of fabricating a semiconductor integrated circuit device, as defined in claim 64, wherein a sidewall film is formed on the surfaces of the sides of said gate electrode and said source/drain regions are then formed by using the sidewall film as a mask.

66. A method of fabricating a semiconductor integrated circuit device, as defined in claim 64, wherein said sputter etching is carried out after the surface of said source/drain regions has been cleaned by using hydrofluoric acid as a cleaning agent.

67. A method of fabricating a semiconductor integrated circuit device, as defined in claim 1, wherein said sputter etching is Ar sputter etching.

68. A method of fabricating a semiconductor integrated circuit device, as defined in claim 64, wherein said metal film is a film of Co.
69. A method of fabricating a semiconductor integrated circuit device, as defined in claim 64, wherein said MISFETs configure an SRAM memory cell.
70. A method of fabricating a semiconductor integrated circuit device, as defined in claim 64, wherein a metal film is formed on said source/drain regions, under near-vacuum conditions, in the same apparatus in which said sputter etching has been carried out.

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